

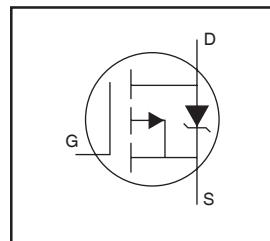
HEXFET® Power MOSFET

Features

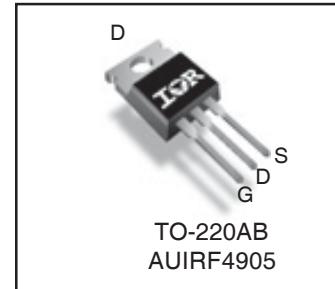
- Advanced Planar Technology
- Low On-Resistance
- Dynamic dV/dT Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to T_{jmax}
- Lead-Free, RoHS Compliant
- Automotive Qualified *

Description

Specifically designed for Automotive applications, this cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.



$V_{(BR)DSS}$	- 55V
$R_{DS(on)}$ max.	0.02Ω
I_D	-74A



G	D	S
Gate	Drain	Source

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10\text{V}$	-74	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10\text{V}$	-52	
I_{DM}	Pulsed Drain Current ①	-260	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	200	W
	Linear Derating Factor	1.3	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy(Thermally limited) ②	930	mJ
I_{AR}	Avalanche Current ①	-38	A
E_{AR}	Repetitive Avalanche Energy ①	20	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-5.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds(1.6mm from case)		
	Mounting Torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{θJC}$	Junction-to-Case ⑦	—	0.75	°C/W
$R_{θCS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{θJA}$	Junction-to-Ambient	—	62	

HEXFET® is a registered trademark of International Rectifier.

*Qualification standards can be found at <http://www.irf.com/>

Static Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(\text{BR})\text{DSS}}$	Drain-to-Source Breakdown Voltage	-55	—	—	V	$V_{\text{GS}} = 0\text{V}$, $I_D = -250\mu\text{A}$
$\Delta V_{(\text{BR})\text{DSS}}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.05	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = -1\text{mA}$
$R_{\text{DS}(\text{on})}$	Static Drain-to-Source On-Resistance	—	—	0.02	Ω	$V_{\text{GS}} = -10\text{V}$, $I_D = -38\text{A}$ ④
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	-2.0	—	-4.0	V	$V_{\text{DS}} = V_{\text{GS}}$, $I_D = -250\mu\text{A}$
g_{fs}	Forward Transconductance	21	—	—	S	$V_{\text{DS}} = -25\text{V}$, $I_D = -38\text{A}$
I_{DSS}	Drain-to-Source Leakage Current	—	—	-25	μA	$V_{\text{DS}} = -55\text{V}$, $V_{\text{GS}} = 0\text{V}$
		—	—	-250		$V_{\text{DS}} = -44\text{V}$, $V_{\text{GS}} = 0\text{V}$, $T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{\text{GS}} = 20\text{V}$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{\text{GS}} = -20\text{V}$

Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

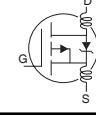
Q_g	Total Gate Charge	—	—	180	nC	$I_D = -38\text{A}$ $V_{\text{DS}} = -44\text{V}$ $V_{\text{GS}} = -10\text{V}$, See Fig.6 and 13 ④
Q_{gs}	Gate-to-Source Charge	—	—	32		
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	86		
$t_{\text{d}(\text{on})}$	Turn-On Delay Time	—	18	—		
t_r	Rise Time	—	99	—	ns	$V_{\text{DD}} = -28\text{V}$ $I_D = -38\text{A}$ $R_G = 2.5 \Omega$ $R_D = 0.72 \Omega$ See Fig. 10 ④
$t_{\text{d}(\text{off})}$	Turn-Off Delay Time	—	61	—		
t_f	Fall Time	—	96	—		
L_{D}	Internal Drain Inductance	—	4.5	—		
L_{S}	Internal Source Inductance	—	7.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
C_{iss}	Input Capacitance	—	3400	—	pF	$V_{\text{GS}} = 0\text{V}$
C_{oss}	Output Capacitance	—	1400	—		$V_{\text{DS}} = -25\text{V}$
C_{rss}	Reverse Transfer Capacitance	—	640	—		$f = 1.0\text{MHz}$, See Fig.5

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_s	Continuous Source Current (Body Diode)	—	—	-74	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-260		
V_{SD}	Diode Forward Voltage	—	—	-1.6		$T_J = 25^\circ\text{C}$, $I_s = -38\text{A}$, $V_{\text{GS}} = 0\text{V}$ ④
t_{rr}	Reverse Recovery Time	—	89	130	ns	$T_J = 25^\circ\text{C}$, $I_F = -38\text{A}$ $di/dt = -100\text{A}/\mu\text{s}$ ④
Q_{rr}	Reverse Recovery Charge	—	230	350	nC	
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Starting $T_J = 25^\circ\text{C}$, $L = 1.3\text{mH}$ $R_G = 25\Omega$, $I_{AS} = -38\text{A}$. (See Figure 12)③ $I_{SD} \leq -38\text{A}$, $di/dt \leq -270\text{A}/\mu\text{s}$, $V_{\text{DD}} \leq V_{(\text{BR})\text{DSS}}$, $T_J \leq 175^\circ\text{C}$ ④ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

Qualification Information[†]

Qualification Level		Automotive (per AEC-Q101) ^{††}	
Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.			
Moisture Sensitivity Level		3L-TO-220	N/A
ESD	Machine Model	Class M4 (425V) (per AEC-Q101-002)	
	Human Body Model	Class H2 (4000V) (per AEC-Q101-001)	
	Charged Device Model	Class C5 (1125V) (per AEC-Q101-005)	
RoHS Compliant		Yes	

[†] Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

^{††} Exceptions to AEC-Q101 requirements are noted in the qualification report.

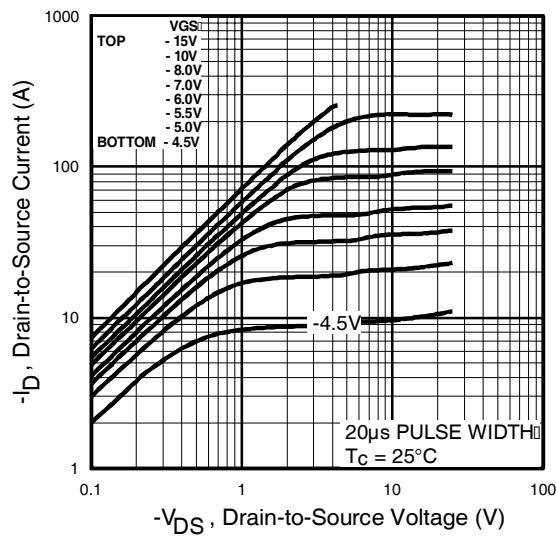


Fig 1. Typical Output Characteristics

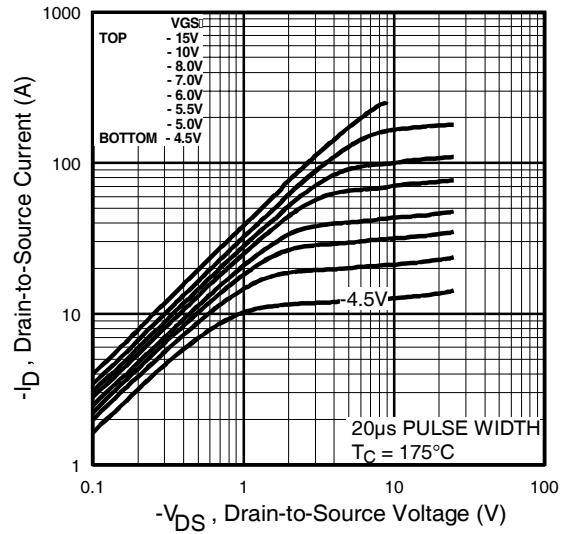


Fig 2. Typical Output Characteristics

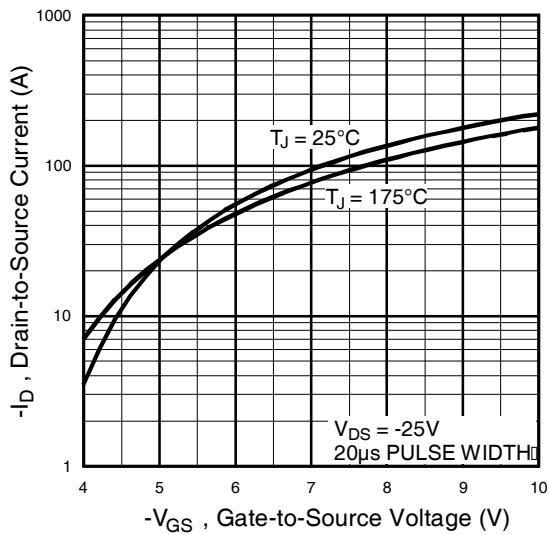


Fig 3. Typical Transfer Characteristics

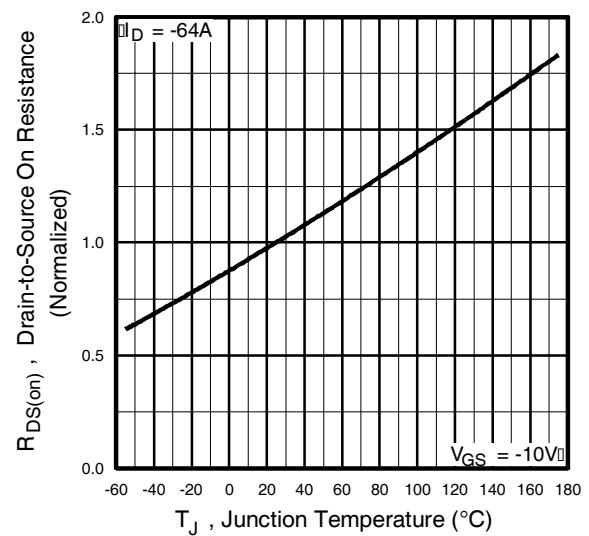


Fig 4. Normalized On-Resistance Vs. Temperature

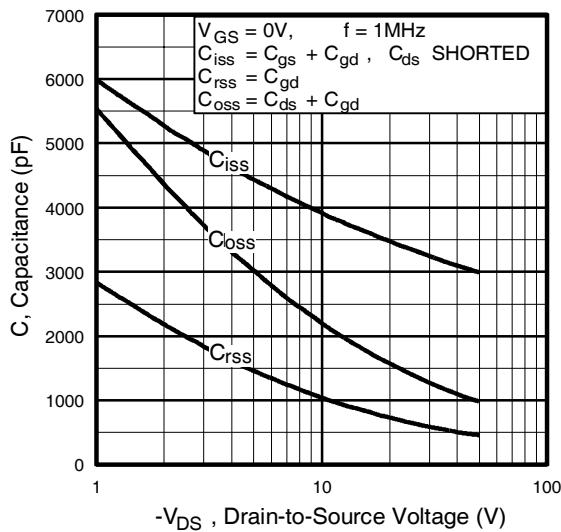


Fig 5. Typical Capacitance Vs.
Drain-to-Source Voltage

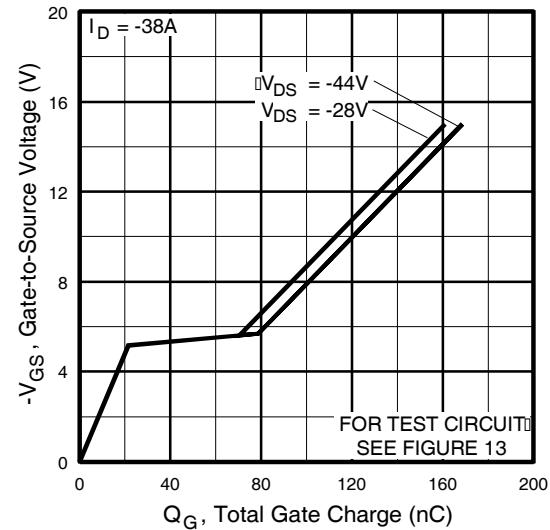


Fig 6. Typical Gate Charge Vs.
Gate-to-Source Voltage

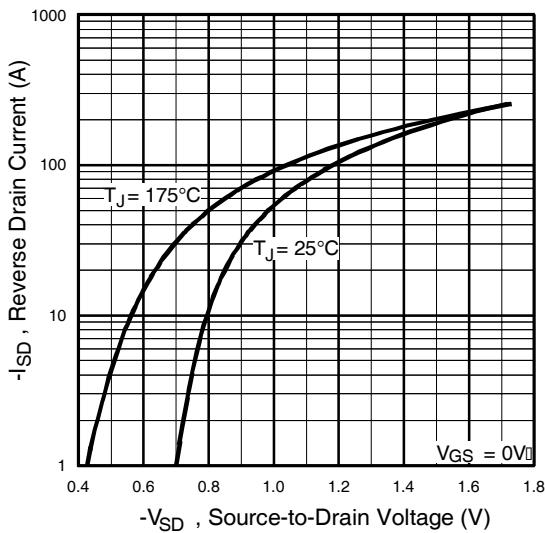


Fig 7. Typical Source-Drain Diode
Forward Voltage

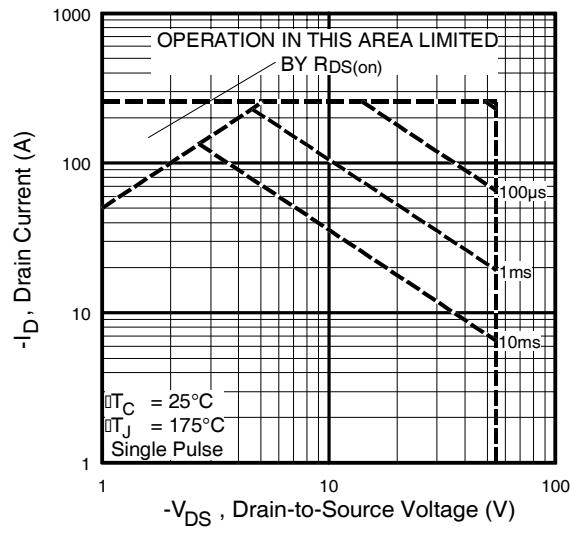


Fig 8. Maximum Safe Operating Area

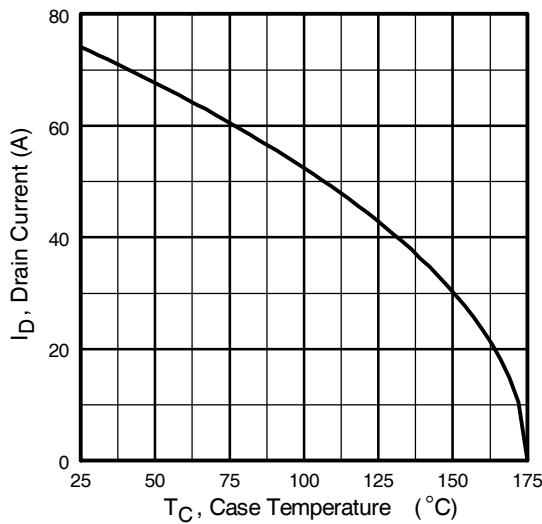


Fig 9. Maximum Drain Current Vs.
Case Temperature

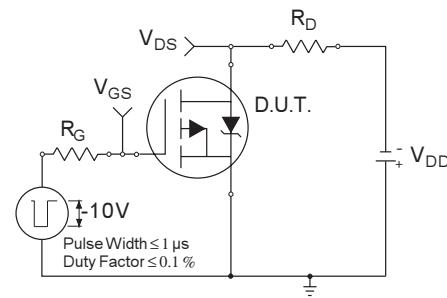


Fig 10a. Switching Time Test Circuit

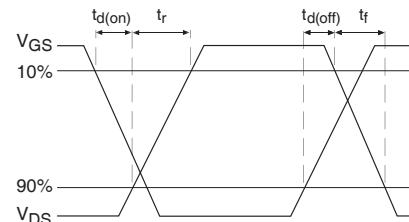


Fig 10b. Switching Time Waveforms

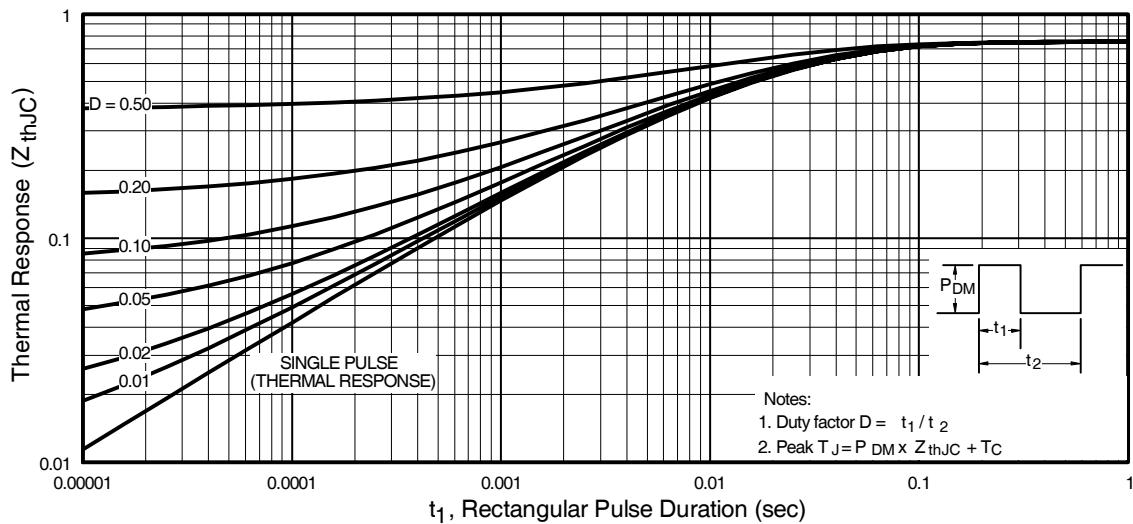


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

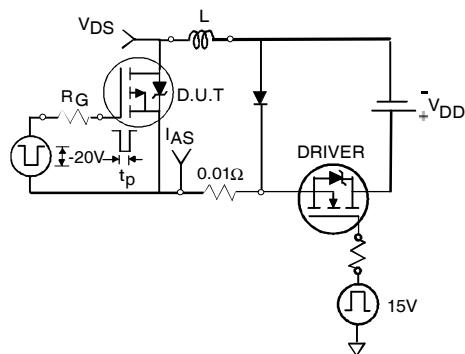


Fig 12a. Unclamped Inductive Test Circuit

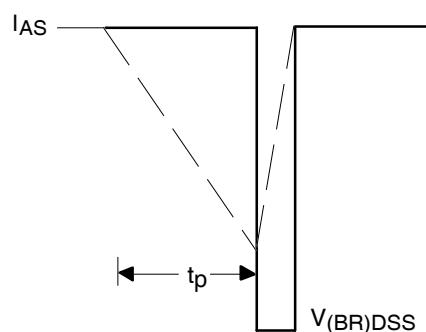


Fig 12b. Unclamped Inductive Waveforms

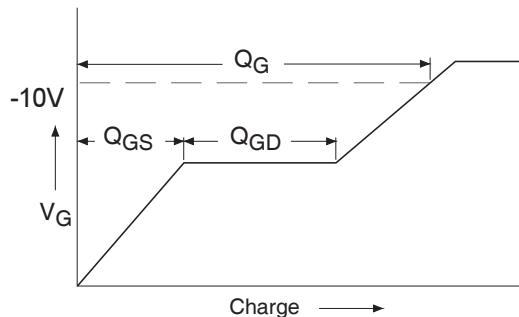


Fig 13a. Basic Gate Charge Waveform

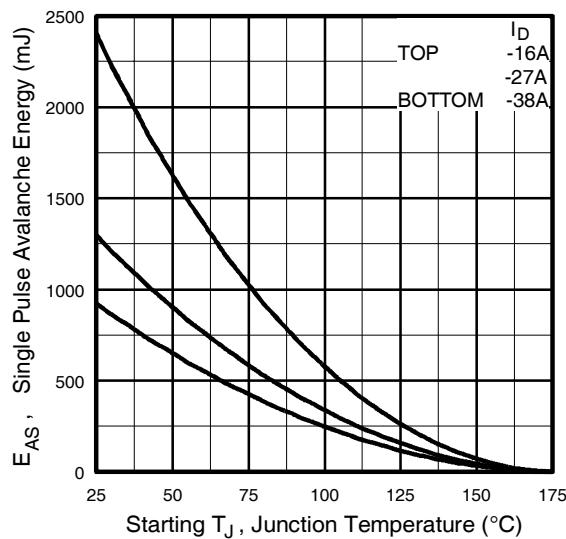


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

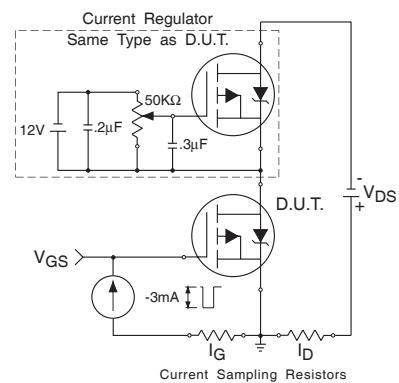
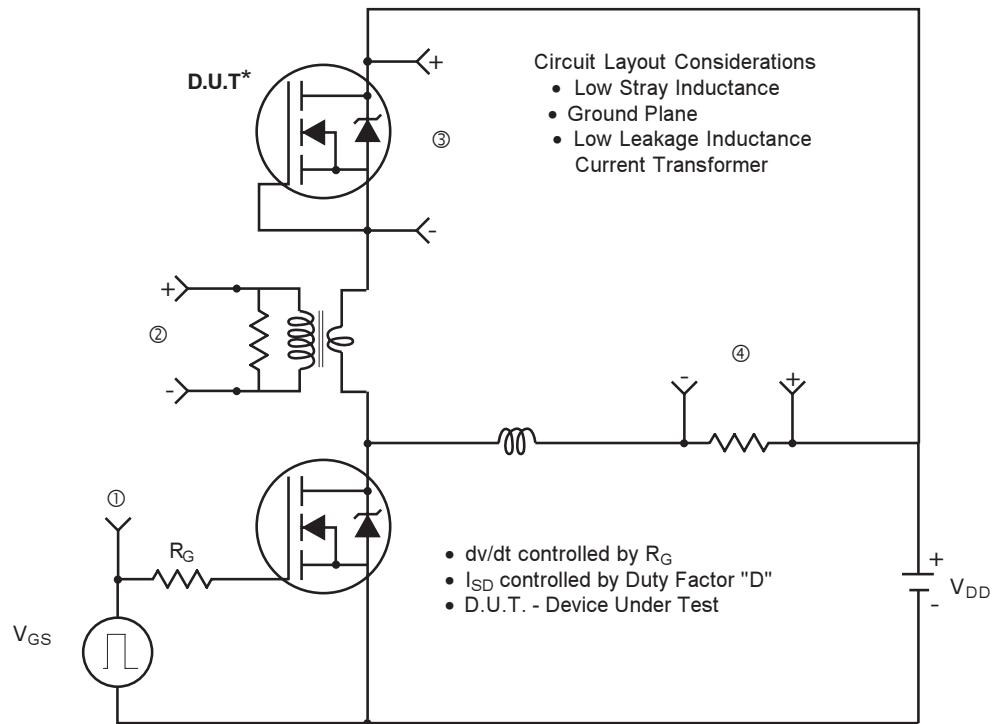
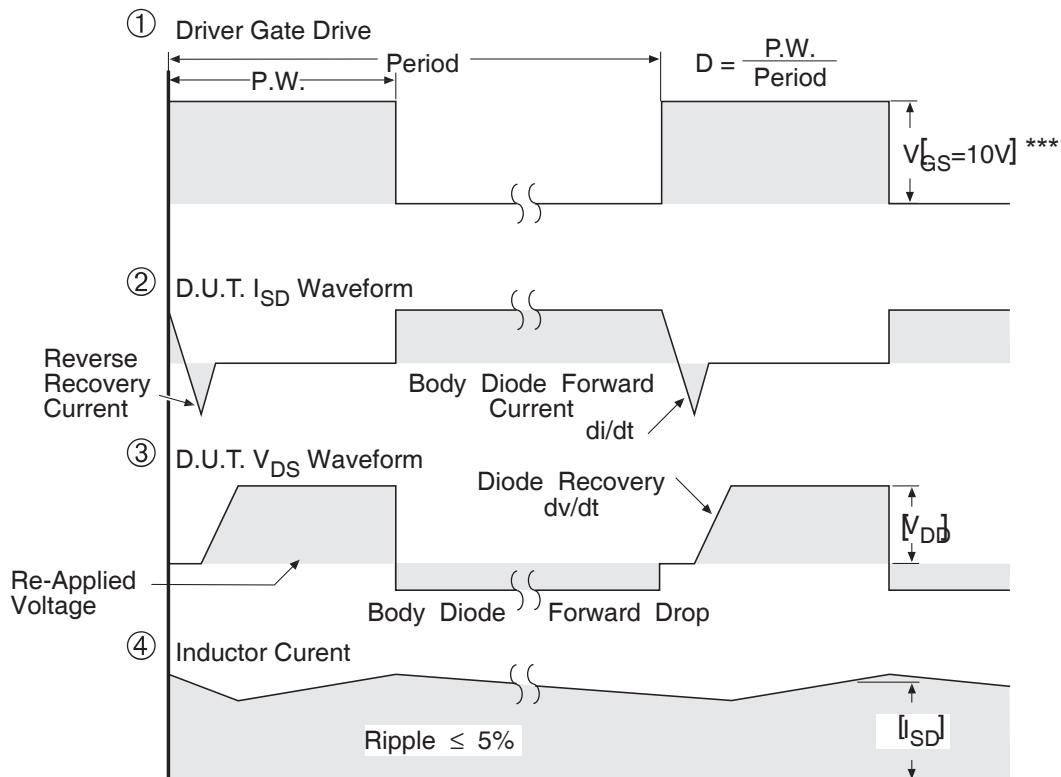


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit

* Reverse Polarity of D.U.T for P-Channel

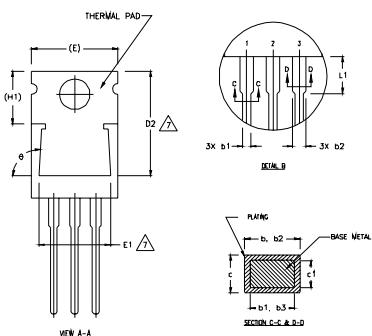
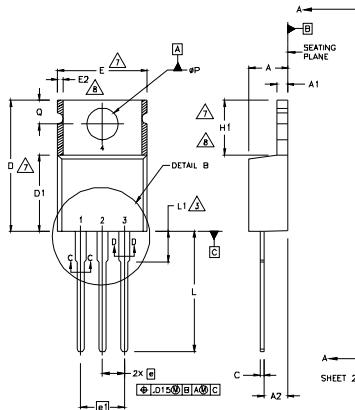


*** $V_{GS} = 5.0V$ for Logic Level and 3V Drive Devices

Fig 14. For P-Channel HEXFETs

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
2. DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
3. LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. DIMENSION b1 & c1 APPLY TO BASE METAL ONLY.
6. CONTROLLING DIMENSION : INCHES.
7. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E1,H1,D2 & E2
8. DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE

IGBTs_COPACK

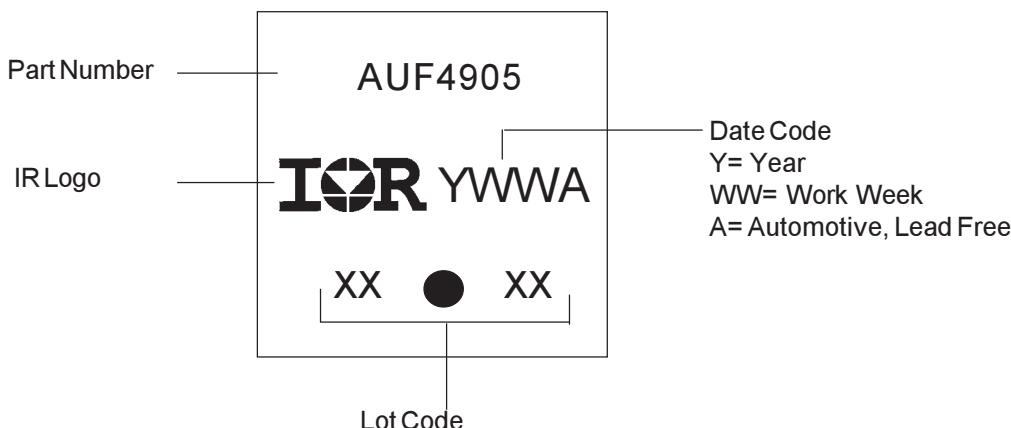
- 1.- GATE
- 2.- COLLECTOR
- 3.- Emitter

DIODES

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

SYMBOL	DIMENSIONS				NOTES	
	MILLIMETERS		INCHES			
	MIN.	MAX.	MIN.	MAX.		
A	3.56	4.82	.140	.190		
A1	0.51	1.40	.020	.055		
A2	2.04	2.92	.080	.115		
b	0.38	1.01	.015	.040		
b1	0.38	0.96	.015	.038	5	
b2	1.15	1.77	.045	.070		
b3	1.15	1.73	.045	.068		
c	0.36	0.61	.014	.024		
c1	0.36	0.56	.014	.022	5	
D	14.22	16.51	.560	.650	4	
D1	8.38	9.02	.330	.355		
D2	12.19	12.88	.480	.507	7	
E	9.66	10.66	.380	.420	4,7	
E1	8.38	8.89	.330	.350	7	
e	2.54	BSC	.100	BSC		
e1	5.08		.200	BSC		
H1	5.85	6.55	.230	.270	7,8	
L	12.70	14.73	.500	.580		
L1	—	6.35	—	.250	3	
ØP	3.54	4.08	.139	.161		
Q	2.54	3.42	.100	.135		
Ø	90°-93°		90°-93°			

TO-220AB Part Marking Information



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>
www.irf.com

Ordering Information

Base part	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRF4905	TO-220	Tube	50	AUIRF4905

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